

LISTING OF CLAIMS:

1 (previously presented) A slurry for chemical mechanical polishing (CMP) a metal surface of a semiconductor substrate with a polyurethane free thermoplastic foam polishing body, comprising,

an acid buffer that maintains said slurry at a pH between about 2.5 and about 4.0 during polishing of a metal surface on a semiconductor substrate; and

an abrasive particle stabilizer, wherein said abrasive particle stabilizer comprises molecules that are equivalent to repeating units of polymers comprising abrasive particles in said slurry.

2 (original) The slurry as recited in Claim 1, wherein said pH is between about 2.7 and about 3.2.

3. (original) The slurry as recited in Claim 1, wherein said pH is between about 3.5 and about 4.0.

Claim 4 (canceled)

5. (previously presented) The slurry as recited in Claim 1, wherein said abrasive particles comprise colloidal silica particles and said abrasive particle stabilizer comprises silicic acid and silicic salt.

6. (original) The slurry as recited in Claim 5, wherein a ratio of said silicic acid to said silicic salt is between about 100:1 and 1:100.

7. (previously presented) The slurry as recited in Claim 1, wherein said abrasive particles comprise alumina and said abrasive particle stabilizer comprises aluminate salts.

8. (original) The slurry as recited in Claim 1, further including an oxidant and a passivation agent.

9. (original) The slurry as recited in Claim 8, wherein said passivation agent is generated *in situ* from a reaction between said metal surface and said oxidant.

10. (original) The slurry as recited in Claim 9, wherein said oxidant is potassium iodate (KIO_3) said passivation agent is iodine (I_2) and said metal surface includes copper.

11. (original) The slurry as recited in Claim 9, further including a second passivation agent that is not generated *in situ* wherein said passivation agent and said second passivation agent synergistically interact with said metal surface to retard corrosion of said metal surface.